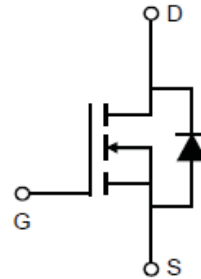


## N-Channel Super Trench Power MOSFET

### Description

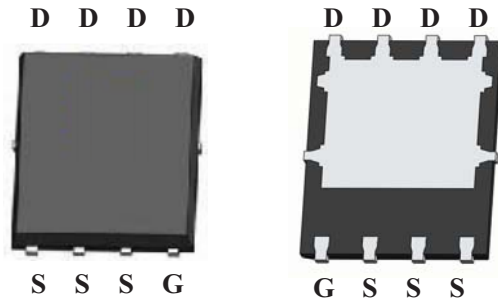
The RM150N40DF uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.



Schematic Diagram

### General Features

- $V_{DS} = 40V, I_D = 150A$   
 $R_{DS(ON)} = 1.72m$  (typical) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 2.3m$  (typical) @  $V_{GS} = 4.5V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested



Top View

Bottom View

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free

**100% UIS TESTED!**  
**100%  $\Delta V_d$ s TESTED!**

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FN40	RM150N40DF	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous ( <b>Silicon Limited</b> )	$I_D$	150	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	106	A
Pulsed Drain Current ( <b>Package Limited</b> )	$I_{DM}$	400	A
Maximum Power Dissipation	$P_D$	88	W
Derating factor		0.7	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	720	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.42	$^{\circ}\text{C}/\text{W}$
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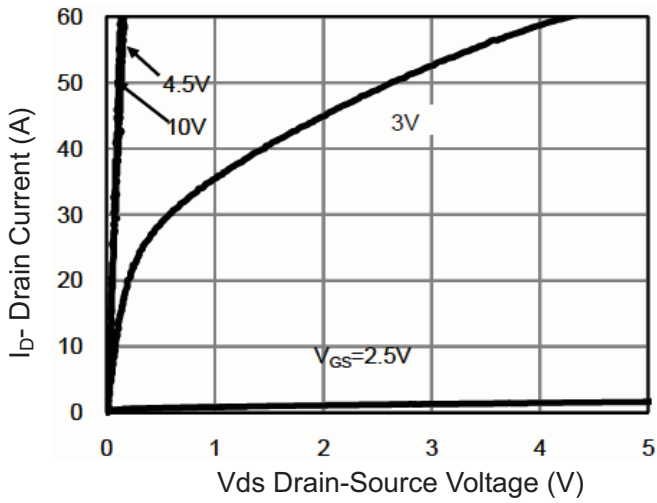
## Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=75A$	-	1.72	2.1	m
		$V_{GS}=4.5V, I_D=75A$	-	2.3	2.8	m
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=75A$	-	80	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	6000	7150	PF
Output Capacitance	$C_{oss}$		-	1450	1700	PF
Reverse Transfer Capacitance	$C_{rss}$		-	100	145	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=75A$ $V_{GS}=10V, R_G=1.6\Omega$	-	12.5	-	nS
Turn-on Rise Time	$t_r$		-	7.0	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	$t_f$		-	8.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=75A,$ $V_{GS}=10V$	-	95	115	nC
Gate-Source Charge	$Q_{gs}$		-	15		nC
Gate-Drain Charge	$Q_{gd}$		-	11		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=75A$	-		1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	150	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = I_S$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-		31	nS
Reverse Recovery Charge	$Q_{rr}$		-		110	nC

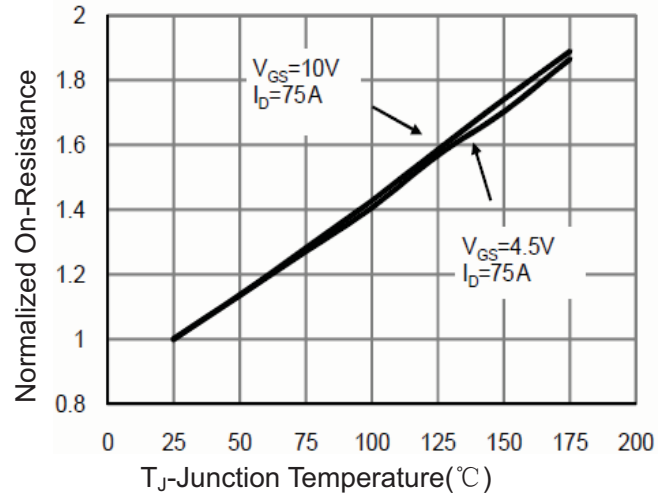
### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

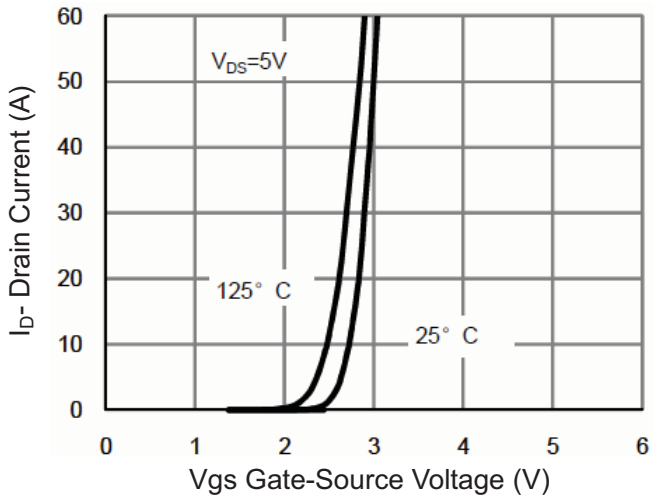
## RATING AND CHARACTERISTICS CURVES (RM150N40DF)



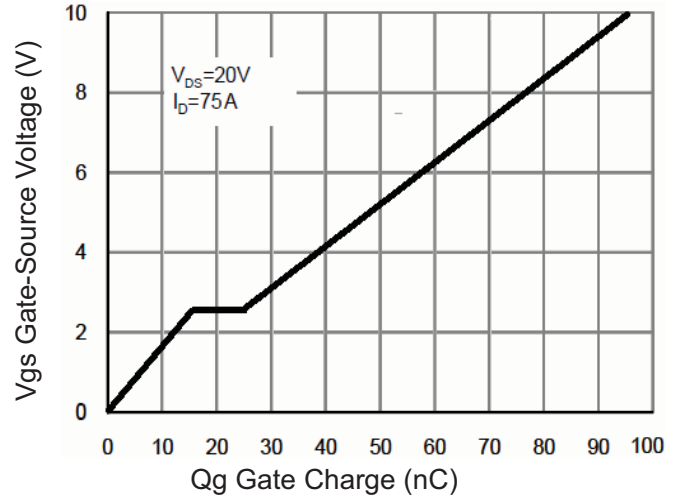
**Figure 1 Output Characteristics**



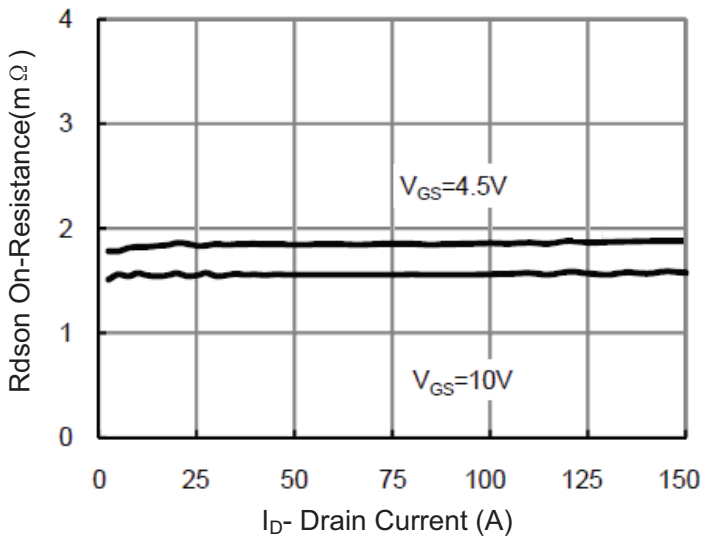
**Figure 4  $R_{dson}$ -Junction Temperature**



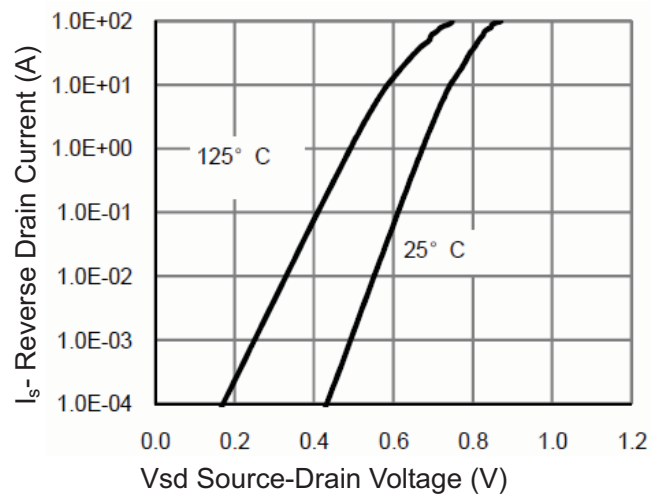
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3  $R_{dson}$ - Drain Current**



**Figure 6 Source- Drain Diode Forward**

## RATING AND CHARACTERISTICS CURVES (RM150N40DF)

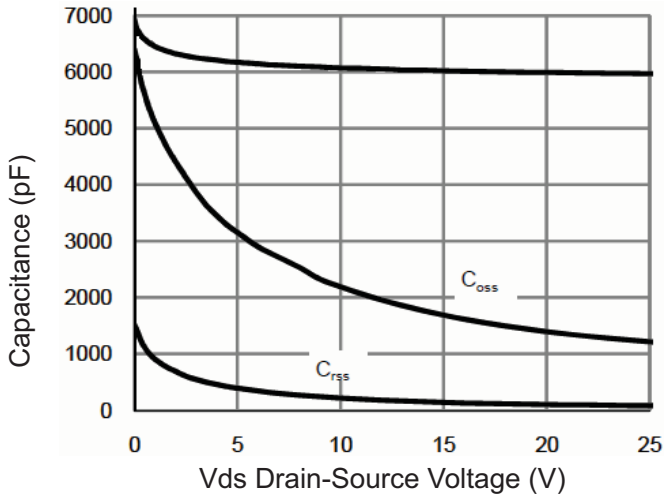


Figure 7 Capacitance vs Vds

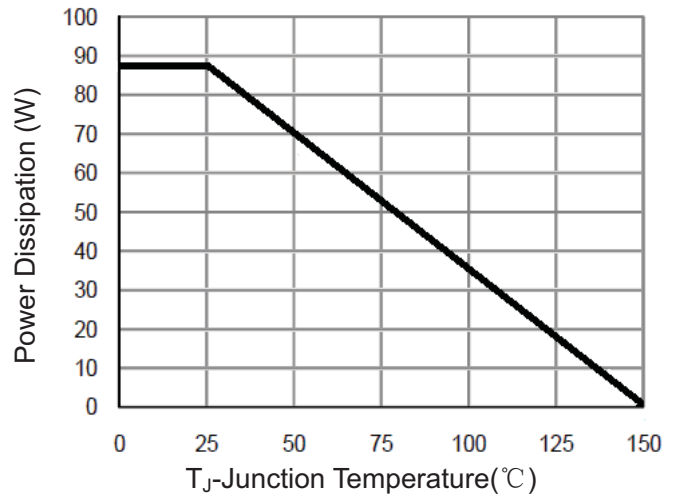


Figure 9 Power De-rating

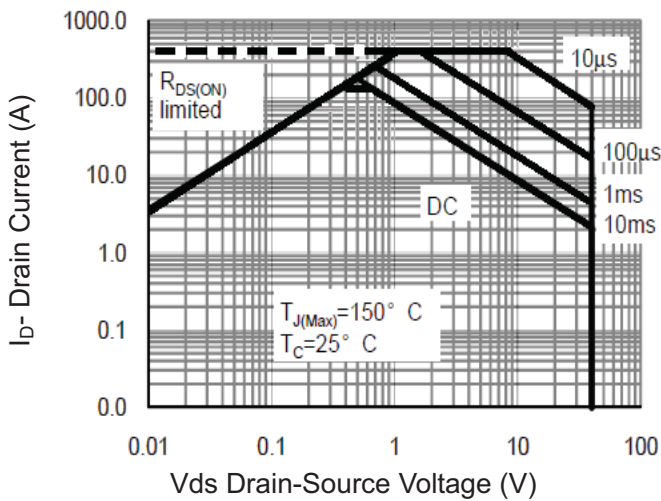


Figure 8 Safe Operation Area

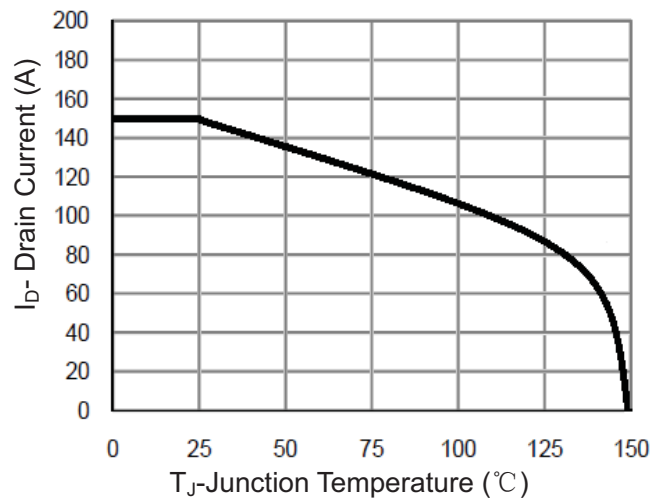


Figure 10 Current De-rating

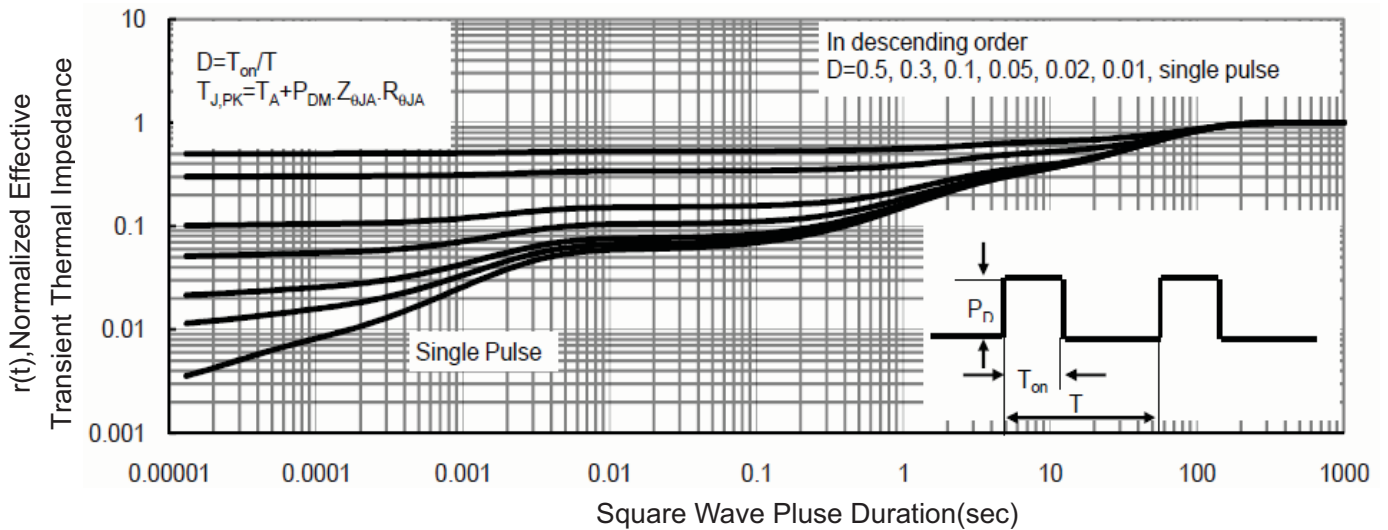
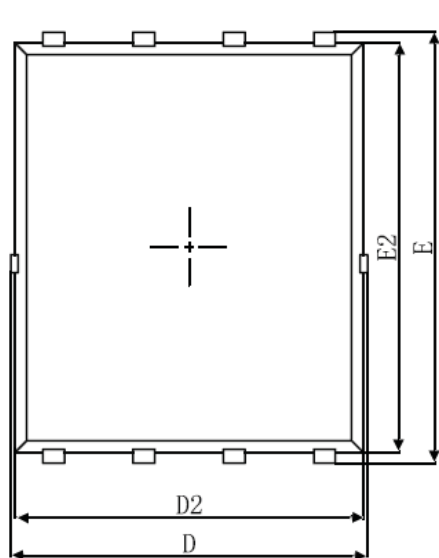
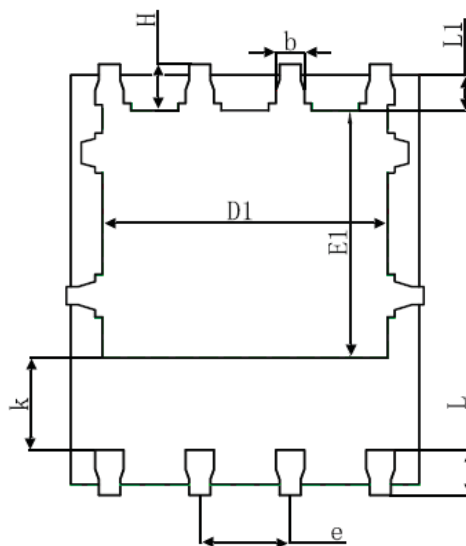


Figure 11 Normalized Maximum Transient Thermal Impedance

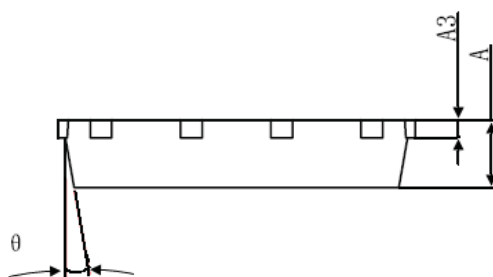
## DFN5X6-8L Package Information



Top View  
[顶视图]



Bottom View  
[背视图]



Side View  
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	8°	12°	8°	12°